

# General-Purpose CMOS Rail-to-Rail Amplifiers

## AD8541/AD8542/AD8544

#### **FEATURES**

Single Supply Operation: 2.7 V to 5.5 V Low Supply Current: 45 μA/Amplifier

Wide Bandwidth: 1 MHz No Phase Reversal Low Input Currents: 4 pA Unity Gain Stable

Rail-to-Rail Input and Output

### **APPLICATIONS**

ASIC Input or Output Amplifier Sensor Interface Piezo Electric Transducer Amplifier Medical Instrumentation Mobile Communication Audio Output Portable Systems

#### **GENERAL DESCRIPTION**

The AD8541/AD8542/AD8544 are single, dual and quad rail-to-rail input and output single supply amplifiers featuring very low supply current and 1 MHz bandwidth. All are guaranteed to operate from a 2.7 V single supply as well as a 5 V supply. These parts provide 1 MHz bandwidth at low current consumption of 45  $\mu$ A per amplifier.

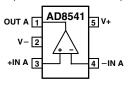
Very low input bias currents enable the AD8541/AD8542/AD8544 to be used for integrators, photodiode amplifiers, piezo electric sensors and other applications with high source impedance. Supply current is only 45  $\mu$ A per amplifier, ideal for battery operation.

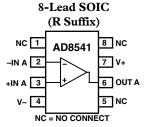
Rail-to-rail inputs and outputs are useful to designers buffering ASICs in single supply systems. The AD8541/AD8542/AD8544 are optimized to maintain high gains at lower supply voltages, making them useful for active filters and gain stages.

The AD8541/AD8542/AD8544 are specified over the extended industrial (-40°C to +125°C) temperature range. The AD8541 is available in 8-lead SOIC, 5-lead SC70, and 5-lead SOT-23 packages. The AD8542 is available in 8-lead SOIC, 8-lead MSOP, and 8-lead TSSOP surface-mount packages. The AD8544 is available in 14-lead narrow SOIC, and 14-lead TSSOP surface mount packages. All TSSOP, MSOP, SC70, and SOT versions are available in tape and reel only.

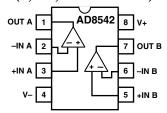
### PIN CONFIGURATIONS

5-Lead SC70 and SOT-23 (KS and RT Suffixes)

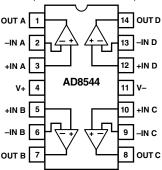




8-Lead SOIC, MSOP, and TSSOP (R, RM, and RU Suffixes)



14-Lead SOIC and TSSOP (R and RU Suffixes)



## REV. B

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## AD8541/AD8542/AD8544—SPECIFICATIONS

**ELECTRICAL CHARACTERISTICS** ( $V_S = 2.7 \text{ V}, V_{CM} = 1.35 \text{ V}, T_A = 25^{\circ}\text{C}$  unless otherwise noted)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	Vos			1	6	mV
		$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$			7	mV
Input Bias Current	$I_B$	4000 455 4 10500		4	60	pA
		$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +85^{\circ}\text{C}$			100	pΑ
Input Offset Current	T	$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$		0.1	1,000 30	pA
input Onset Current	I <sub>OS</sub>	$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +85^{\circ}\text{C}$		0.1	50 50	pA pA
		$-40^{\circ}\text{C} \le T_{A} \le +05^{\circ}\text{C}$ $-40^{\circ}\text{C} \le T_{A} \le +125^{\circ}\text{C}$			500	pA pA
Input Voltage Range		10 0 = 1 <sub>A</sub> = 1123 0	0		2.7	V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = 0 \text{ V to } 2.7 \text{ V}$	40	45		dB
,		$-40^{\circ}$ C $\leq$ T <sub>A</sub> $\leq$ +125 $^{\circ}$ C	38			dB
Large Signal Voltage Gain	$A_{VO}$	$R_L = 100 \text{ k}\Omega$ , $V_O = 0.5 \text{ V}$ to 2.2 V	100	500		V/mV
		$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +85^{\circ}\text{C}$	50			V/mV
		$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$	2			V/mV
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$		4		μV/°C
Bias Current Drift	$\Delta I_{B}/\Delta T$	$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +85^{\circ}\text{C}$		100		fA/°C
Offset Current Drift	AT /AT	$-40^{\circ}\text{C} \le \text{T}_{A} \le +125^{\circ}\text{C}$		2,000		fA/°C fA/°C
	$\Delta I_{OS}/\Delta T$	$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$		25		IA/ C
OUTPUT CHARACTERISTICS						
Output Voltage High	$V_{OH}$	$I_{L} = 1 \text{ mA}$	2.575	2.65		V
Ontrod Walter a Larry	3.7	$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$	2.550	25	100	V
Output Voltage Low	V <sub>OL</sub>	$I_{L} = 1 \text{ mA}$ $-40^{\circ}\text{C} \le T_{A} \le +125^{\circ}\text{C}$		35	100 125	mV mV
Output Current	I <sub>OUT</sub>	$V_{\text{OUT}} = V_{\text{S}} - 1 \text{ V}$		15	123	mA
Output Current	±I <sub>SC</sub>	VOUT - VS - 1 V		±20		mA
Closed Loop Output Impedance	Z <sub>OUT</sub>	$f = 200 \text{ kHz}, A_V = 1$		50		Ω
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_S = 2.5 \text{ V to } 6 \text{ V}$	65	76		dB
,		$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$	60			dB
Supply Current/Amplifier	$I_{SY}$	$V_O = 0 V$		38	55	μΑ
		$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$			75	μΑ
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_L = 100 \text{ k}\Omega$	0.4	0.75		V/µs
Settling Time	t <sub>S</sub>	To 0.1% (1 V Step)		5		μs
Gain Bandwidth Product	GBP			980		kHz
Phase Margin	Фо			63		Degrees
NOISE PERFORMANCE						
Voltage Noise Density	e <sub>n</sub>	f = 1  kHz	1	40		$nV/\sqrt{Hz}$
	e <sub>n</sub>	f = 10 kHz		38		$nV/\sqrt{Hz}$
Current Noise Density	i <sub>n</sub>			< 0.1		pA/√ <del>Hz</del>

Specifications subject to change without notice.

## **ELECTRICAL CHARACTERISTICS** ( $V_S = 3.0 \text{ V}, V_{CM} = 1.5 \text{ V}, T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	Vos			1	6	mV
Innut Dies Coment	т	$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$		4	7 60	mV
Input Bias Current	$I_{\mathrm{B}}$	$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +85^{\circ}\text{C}$		4	100	pA pA
		$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$			1,000	pA
Input Offset Current	$I_{OS}$			0.1	30	pA
		$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +85^{\circ}\text{C}$			50	pA
Input Voltage Range		$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$	0		500 3	pA V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = 0 \text{ V to } 3 \text{ V}$	40	45	3	dB
Common Nzoue Rejection Rutio	Givinat	$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$	38	13		dB
Large Signal Voltage Gain	A <sub>VO</sub>	$R_{L} = 100 \text{ k}\Omega$ , $V_{O} = 0.5 \text{ V}$ to 2.2 V	100	500		V/mV
		$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +85^{\circ}\text{C}$	50			V/mV
Office Walter Dolfe	A \$ 7 / A TE	$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$	2	4		V/mV
Offset Voltage Drift Bias Current Drift	$\Delta V_{OS}/\Delta T$ $\Delta I_{B}/\Delta T$	$ -40^{\circ}C \le T_{A} \le +125^{\circ}C  -40^{\circ}C \le T_{A} \le +85^{\circ}C $		4 100		μV/°C fA/°C
Dias Guirent Dint	Δ <b>1</b> Β/Δ <b>1</b>	$-40^{\circ}\text{C} \le T_{A} \le +125^{\circ}\text{C}$		2,000		fA/°C
Offset Current Drift	$\Delta I_{OS}/\Delta T$	$-40^{\circ}\text{C} \le \text{T}_{\text{A}}^{\text{C}} \le +125^{\circ}\text{C}$		25		fA/°C
OUTPUT CHARACTERISTICS						
Output Voltage High	$V_{OH}$	$I_L = 1 \text{ mA}$	2.875	2.955		V
		$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$	2.850			V
Output Voltage Low	V <sub>OL</sub>	$I_L = 1 \text{ mA}$ -40°C \le T_A \le +125°C		32	100 125	mV
Output Current	$I_{OUT}$	$V_{OUT} = V_S - 1 V$		18	125	mV mA
output durient	$\pm I_{SC}$	V001 VS 1 V		±25		mA
Closed Loop Output Impedance	$Z_{OUT}$	$f = 200 \text{ kHz}, A_V = 1$		50		Ω
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_S = 2.5 \text{ V to } 6 \text{ V}$	65	76		dB
S 1 C ./A 1'.C'	T	$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$	60	40	60	dB
Supply Current/Amplifier	$I_{SY}$	$V_{O} = 0 \text{ V}$ -40°C \le T_{A} \le +125°C		40	60 75	μA μA
DVNIAMIC DEDEODMANOS		10 0 2 1 <sub>A</sub> 2 + 125 0			1.5	μι
DYNAMIC PERFORMANCE Slew Rate	SR	$R_{I} = 100 \text{ k}\Omega$	0.4	0.8		V/µs
Settling Time	t <sub>S</sub>	To 0.01% (1 V Step)	0.4	5		μs
Gain Bandwidth Product	GBP	1,		980		kHz
Phase Margin	Фо			64		Degrees
NOISE PERFORMANCE						
Voltage Noise Density	e <sub>n</sub>	f = 1  kHz		42		nV/√ <u>Hz</u>
Compant Naisa Danaitra	e <sub>n</sub>	f = 10 kHz		38		$nV/\sqrt{Hz}$
Current Noise Density	i <sub>n</sub>			<0.1		pA/√ <del>Hz</del>

Specifications subject to change without notice.

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## AD8541/AD8542/AD8544—SPECIFICATIONS

## **ELECTRICAL CHARACTERISTICS** ( $V_S = 5.0 \text{ V}, V_{CM} = 2.5 \text{ V}, T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	Vos			1	6	mV
		$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$			7	mV
Input Bias Current	$I_B$			4	60	pA
		$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +85^{\circ}\text{C}$			100	pA
		$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$			1,000	pA
Input Offset Current	I <sub>OS</sub>			0.1	30	pA
		$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +85^{\circ}\text{C}$			50	pA
		$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$			500	pA
Input Voltage Range			0		5	V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = 0 \text{ V to 5 V}$	40	48		dB
		$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$	38			dB
Large Signal Voltage Gain	$A_{VO}$	$R_L = 100 \text{ k}\Omega$ , $V_O = 0.5 \text{ V}$ to 2.2 V	20	40		V/mV
		$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +85^{\circ}\text{C}$	10			V/mV
O.C II 1 D C.	AXX /AFD	$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$	2			V/mV
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	$-40^{\circ}\text{C} \le \text{T}_{A} \le +125^{\circ}\text{C}$		4		μV/°C
Bias Current Drift	$\Delta I_{B}/\Delta T$	$-40^{\circ}\text{C} \le \text{T}_{A} \le +85^{\circ}\text{C}$		100		fA/°C fA/°C
Offset Current Drift	$\Delta I_{OS}/\Delta T$	$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$ $-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$		2,000 25		fA/°C
	ΔΙΟς/ΔΙ	-40 C S 1 <sub>A</sub> S +123 C	-			IA/ C
OUTPUT CHARACTERISTICS						
Output Voltage High	$V_{OH}$	$I_L = 1 \text{ mA}$	4.9	4.965		V
		$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$	4.875			V
Output Voltage Low	V <sub>OL</sub>	$I_{L} = 1 \text{ mA}$		25	100	mV
0 0		$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$		20	125	mV
Output Current	I <sub>OUT</sub>	$V_{OUT} = V_S - 1 V$		30		mA
Closed I can Outnut Immedance	±I <sub>SC</sub>	f = 200 I-II- A = 1		±60 45		$MA$ $\Omega$
Closed Loop Output Impedance	Z <sub>OUT</sub>	$f = 200 \text{ kHz}, A_V = 1$		40		52
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_{\rm S} = 2.5 \text{ V to } 6 \text{ V}$	65	76		dB
	_	$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$	60			dB
Supply Current/Amplifier	$I_{SY}$	$V_0 = 0 \text{ V}$		45	65	μA
		$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$			85	μA
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_L = 100 \text{ k}\Omega, C_L = 200 \text{ pF}$	0.45	0.92		V/µs
Full-Power Bandwidth	$BW_P$	1% Distortion		70		kHz
Settling Time	$t_S$	To 0.1% (1 V Step)		6		μs
Gain Bandwidth Product	GBP			1,000		kHz
Phase Margin	Фо			67		Degrees
NOISE PERFORMANCE						
Voltage Noise Density	e <sub>n</sub>	f = 1  kHz		42		$nV/\sqrt{Hz}$
-	e <sub>n</sub>	f = 10 kHz		38		$nV/\sqrt{Hz}$
Current Noise Density	i <sub>n</sub>			< 0.1		pA/√ <del>Hz</del>

Specifications subject to change without notice.

## ABSOLUTE MAXIMUM RATINGS1

Supply Voltage (V <sub>S</sub> ) 6 V
Input Voltage GND to V <sub>S</sub>
Differential Input Voltage <sup>2</sup>
Storage Temperature Range65°C to +150°C
Operating Temperature Range40°C to +125°C
Junction Temperature Range –65°C to +150°C
Lead Temperature Range (Soldering, 60 sec) 300°C
NOTES

<sup>1</sup>Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### PACKAGE INFORMATION

Package Type	$\theta_{JA}^*$	$\theta_{ m JC}$	Unit
5-Lead SC70 (KS)	376	126	°C/W
5-Lead SOT-23 (RT)	230	146	°C/W
8-Lead SOIC (R)	158	43	°C/W
8-Lead MSOP (RM)	210	45	°C/W
8-Lead TSSOP (RU)	240	43	°C/W
14-Lead SOIC (R)	120	36	°C/W
14-Lead TSSOP (RU)	240	43	°C/W

<sup>\*</sup>θ<sub>JA</sub> is specified for worst-case conditions, i.e., q<sub>JA</sub> is specified for device soldered onto a circuit board for surface mount packages.

#### **ORDERING GUIDE**

Model	Temperature Range	Package Description	Package Option	Branding Information
AD8541AKS*	−40°C to +125°C	5-Lead SC70	KS-5	A4B
AD8541AR	−40°C to +125°C	8-Lead SOIC	SO-8	
AD8541ART*	−40°C to +125°C	5-Lead SOT-23	RT-5	A4A
AD8542AR	−40°C to +125°C	8-Lead SOIC	SO-8	
AD8542ARM*	–40°C to +125°C	8-Lead MSOP	RM-8	AVA
AD8542ARU*	−40°C to +125°C	8-Lead TSSOP	RU-8	
AD8544AR	−40°C to +125°C	14-Lead SOIC	SO-14	
AD8544ARU*	−40°C to +125°C	14-Lead TSSOP	RU-14	

<sup>\*</sup>Available in reels only.

#### CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the AD8541/AD8542/AD8544 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high-energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



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<sup>&</sup>lt;sup>2</sup>For supplies less than 6 V, the differential input voltage is equal to  $\pm V_s$ .

## AD8541/AD8542/AD8544—Typical Performance Characteristics

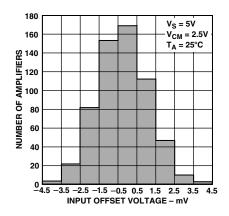


Figure 1. Input Offset Voltage Distribution

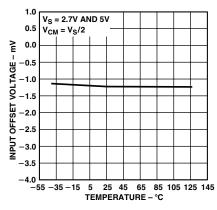


Figure 2. Input Offset Voltage vs. Temperature

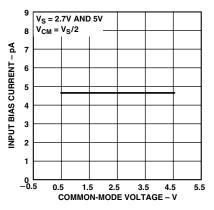


Figure 3. Input Bias Current vs. Common-Mode Voltage

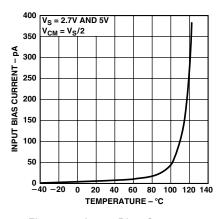


Figure 4. Input Bias Current vs. Temperature

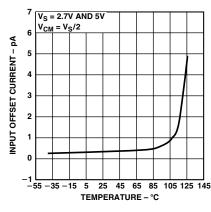


Figure 5. Input Offset Current vs. Temperature

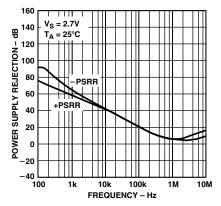


Figure 6. Power Supply Rejection Ratio vs. Frequency

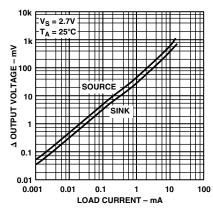


Figure 7. Output Voltage to Supply Rail vs. Load Current

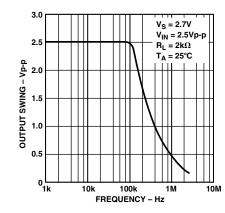


Figure 8. Closed-Loop Output Voltage Swing vs. Frequency

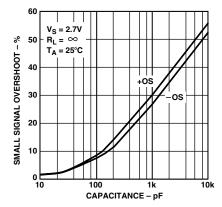


Figure 9. Small Signal Overshoot vs. Load Capacitance

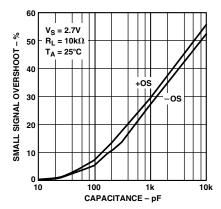


Figure 10. Small Signal Overshoot vs. Load Capacitance

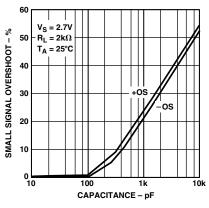


Figure 11. Small Signal Overshoot vs. Load Capacitance

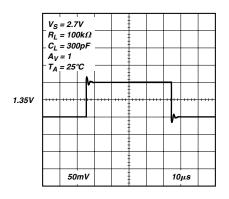


Figure 12. Small Signal Transient Response

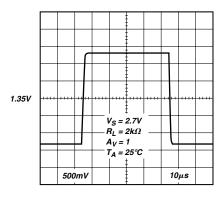


Figure 13. Large Signal Transient Response

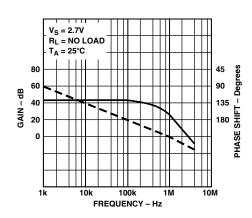


Figure 14. Open-Loop Gain and Phase vs. Frequency

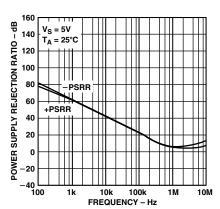


Figure 15. Power Supply Rejection Ratio vs. Frequency

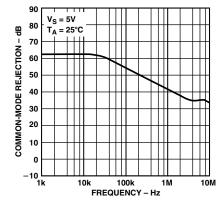


Figure 16. Common-Mode Rejection Ratio vs. Frequency

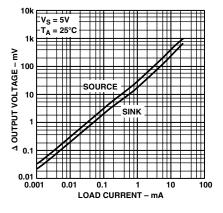


Figure 17. Output Voltage to Supply Rail vs. Frequency

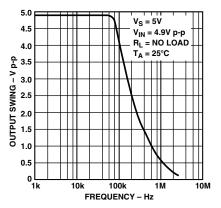


Figure 18. Closed Loop Output Voltage Swing vs. Frequency

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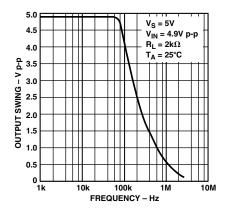


Figure 19. Closed-Loop Output Voltage Swing vs. Frequency

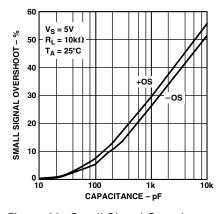


Figure 20. Small Signal Overshoot vs. Load Capacitance

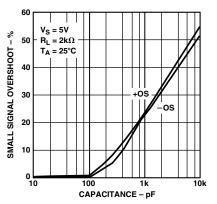


Figure 21. Small Signal Overshoot vs. Load Capacitance

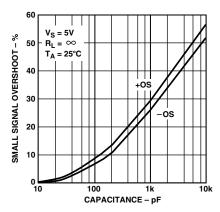


Figure 22. Small Signal Overshoot vs. Load Capacitance

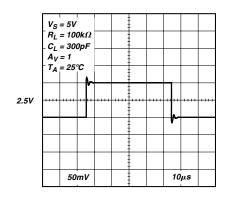


Figure 23. Small Signal Transient Response

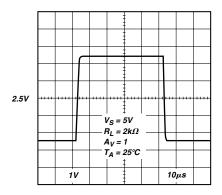


Figure 24. Large Signal Transient Response

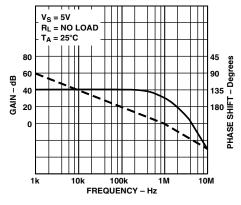


Figure 25. Open-Loop Gain & Phase vs. Frequency

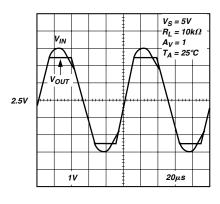


Figure 26. No Phase Reversal

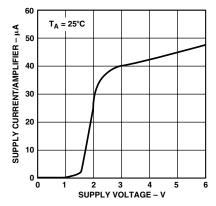


Figure 27. Supply Current per Amplifier vs. Supply Voltage

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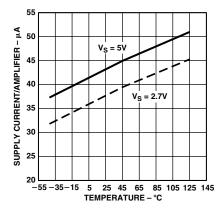


Figure 28. Supply Current per Amplifier vs. Temperature

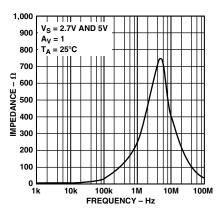


Figure 29. Closed-Loop Output Impedance vs. Frequency

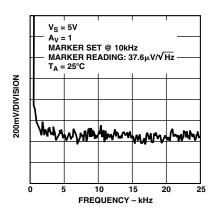


Figure 30. Voltage Noise

### **NOTES ON THE AD854x AMPLIFIERS**

The AD8541/AD8542/AD8544 amplifiers are improved performance general-purpose operational amplifiers. Performance has been improved over previous amplifiers in several ways.

### Lower Supply Current for 1 MHz Gain Bandwidth

The AD854x series typically uses 45 microamps of current per amplifier. This is much less than the 200  $\mu$ A to 700  $\mu$ A used in earlier generation parts with similar performance. This makes the AD854x series a good choice for upgrading portable designs for longer battery life. Alternatively, additional functions and performance can be added at the same current drain.

#### **Higher Output Current**

At 5 V single supply, the short circuit current is typically  $60 \,\mu A$ . Even 1 V from the supply rail, the AD854x amplifiers can provide 30 mA, sourcing or sinking.

Sourcing and sinking is strong at lower voltages, with 15 mA available at 2.7 V, and 18 mA at 3.0 V. For even higher output currents, please see the Analog Devices AD8531/AD8532/AD8534 parts, with output currents to 250 mA. Information on these parts is available from your Analog Devices representative, and data sheets are available at the Analog Devices website at www.analog.com.

### Better Performance at Lower Voltages

The AD854x family parts have been designed to provide better ac performance, at 3.0 V and 2.7 V, than previously available parts. Typical gain-bandwidth product is close to 1 MHz at 2.7 V. Voltage gain at 2.7 V and 3.0 V is typically 500,000. Phase margin is typically over  $60^{\circ}\text{C}$ , making the part easy to use.

## **APPLICATIONS**

#### **Notch Filter**

The AD8542 has very high open loop gain (especially with supply voltage below 4 V), which makes it useful for active filters of all types. For example, Figure 31 illustrates the AD8542 in the classic Twin-T Notch Filter design. The Twin-T Notch is desired for simplicity, low output impedance and minimal use of op amps. In fact, this notch filter may be designed with only one op amp if Q adjustment is not required. Simply remove U2 as illustrated in Figure 32. However, a major drawback to this circuit topology is ensuring that all the Rs and Cs closely match. The components must closely match or notch frequency offset and drift will cause

the circuit to no longer attenuate at the ideal notch frequency. To achieve desired performance, 1% or better component tolerances or special component screens are usually required. One method to desensitize the circuit-to-component mismatch is to increase R2 with respect to R1, which lowers Q. A lower Q increases attenuation over a wider frequency range, but reduces attenuation at the peak notch frequency.

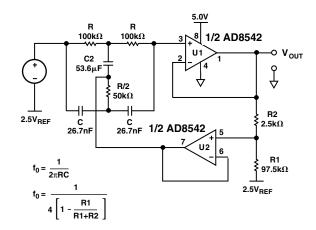


Figure 31. 60 Hz Twin-T Notch Filter, Q = 10

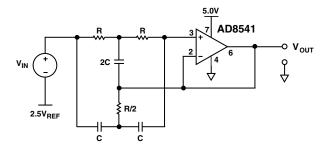


Figure 32. 60 Hz Twin-T Notch Filter,  $Q = \infty$  (Ideal)

Figure 33 diagrams another example of the AD8542 in a notch filter circuit. The FNDR notch filter has several unique features as compared to the Twin-T Notch including: less critical matching requirements; Q is directly proportional to a single resistor R1. While matching component values is still important, it is also much easier and/or less expensive to

accomplish in the FNDR circuit. For example, the Twin-T Notch uses three capacitors with two unique values, whereas the FNDR circuit uses only two capacitors, which may be of the same value. U3 is simply a buffer that is added to lower the output impedance of the circuit.

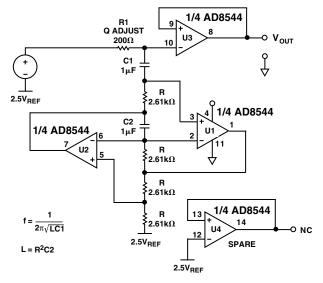


Figure 33. FNDR 60 Hz Notch Filter with Output Buffer

## **Comparator Function**

A comparator function is a common application for a spare op amp in a quad package. Figure 34 illustrates 1/4 of the AD8544 as a comparator in a standard overload detection application. Unlike so many op amps, the AD854x family can double as comparator because this op amp family has rail-to-rail differential input range, rail-to-rail output, and a great speed vs. power ratio. R2 is used to introduce hysteresis. The AD854x when used as comparators have 5  $\mu s$  propagation delay @ 5 V and 5  $\mu s$  overload recovery time.

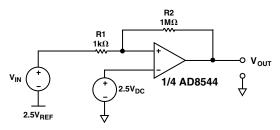


Figure 34. The AD854x Comparator Application–Overload Detector

### Photodiode Application

The AD854x family has very high impedance with input bias current typically around 4 pA. This characteristic allows the AD854x op amps to be used in photodiode applications and other applications that require high input impedance. Note that the AD854x has significant voltage offset, which can be removed by capacitive coupling or software calibration.

Figure 35, illustrates a photodiode or current measurement application. The feedback resistor is limited to 10 M $\Omega$  to avoid excessive output offset. Also note that a resistor is not needed on the noninverting input to cancel bias current offset, because the bias current related output offset is not significant when compared to the voltage offset contribution. For the best performance follow the standard high impedance layout techniques including: shield circuit, clean circuit board, put a trace connected to the noninverting input around the inverting input, and use separate analog and digital power supplies.

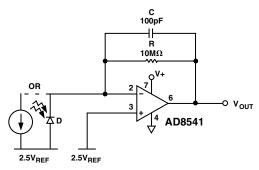


Figure 35. High Input Impedance Application–Photodiode Amplifier

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```
* VOLTAGE NOISE REFERENCE OF 35nV/rt(Hz)
* AD8542 SPICE Macro-model Typical Values
* 6/98, Ver. 1
* TAM / ADSC
                                                     VN1 80 0 0
                                                     RN1 80 0 16.45E-3
* Copyright 1998 by Analog Devices
                                                     HN 81 0 VN1 35
                                                     RN2 81 0 1
* Refer to "README.DOC" file for License State-
ment. Use of this
                                                     * INTERNAL VOLTAGE REFERENCE
* model indicates your acceptance of the terms
and provisions in
                                                     VFIX 90 98 DC 1
* the License Statement.
                                                     S1 90 91 (50,99) VSY SWITCH
                                                     VSN1 91 92 DC 0
* Node Assignments
                                                     RSY 92 98 1E3
                                                     EREF 98 0 POLY(2) (99,0) (50,0) 0 .5 .5
                   noninverting input
                                                     GSY 99 50 POLY(1) (99,50) 0 3.7E-6
                      inverting input
                           positive supply
                                                     * ADAPTIVE GAIN STAGE
                             negative supply
                                 output
                                                     * AT Vsy>+4.2, AVol=45 V/mv
                                                     * AT Vsy<+3.8, AVol=450 V/mv
.SUBCKT AD8542
                                                     G1 98 30 POLY(2) (4,6) (11,12) 0 2.5E-5 2.5E-5
                     2 99 50 45
                   1
                                                     VR1 30 31 DC 0
* INPUT STAGE
                                                     H1 31 98 POLY(2) VR1 VSN1 0 5.45E6 0 0 49.05E9
                                                     CF 45 30 10E-12
M1 4 1 8 8 PIX L=0.6E-6 W=16E-6
                                                     D3 30 99 DX
M2 6 7 8 8 PIX L=0.6E-6 W=16E-6
                                                     D4 50 30 DX
M3 11 1 10 10 NIX L=0.6E-6 W=16E-6
M4 12 7 10 10 NIX L=0.6E-6 W=16E-6
                                                     * OUTPUT STAGE
RC1 4 50 20E3
RC2 6 50 20E3
                                                     M5 45 46 99 99 POX L=0.6E-6 W=375E-6
RC3 99 11 20E3
                                                     M6 45 47 50 50 NOX L=0.6E-6 W=500E-6
RC4 99 12 20E3
                                                     EG1 99 46 POLY(1) (98,30) 1.05 1
C1 4 6 1.5E-12
                                                     EG2 47 50 POLY(1) (30,98) 1.04 1
C2 11 12 1.5E-12
                                                     * MODELS
I1 99 8 1E-5
I2 10 50 1E-5
V1 99 9 0.2
                                                     .MODEL POX PMOS (LEVEL=2, KP=20E-6, VTO=-
V2 13 50 0.2
                                                      +1,LAMBDA=0.067)
D1
   8 9 DX
                                                     .MODEL NOX NMOS (LEVEL=2, KP=20E-
D2 13 10 DX
                                                      +6, VTO=1, LAMBDA=0.067)
EOS 7 2 POLY(3) (22,98) (73,98) (81,0) 1E-3 1 1
                                                     .MODEL PIX PMOS (LEVEL=2, KP=20E-6, VTO=-
                                                      +0.7, LAMBDA=0.01, KF=1E-31)
IOS 1 2 2.5E-12
                                                     .MODEL NIX NMOS (LEVEL=2, KP=20E-
                                                      +6, VTO=0.7, LAMBDA=0.01, KF=1E-31)
* CMRR 64dB, ZERO AT 20kHz
                                                     .MODEL DX D(IS=1E-14)
                                                     .MODEL VSY SWITCH VSWITCH (ROFF=100E3, RON=1, VOFF=-
ECM1 21 98 POLY(2) (1,98) (2,98) 0 .5 .5
                                                     +4.2, VON = -3.5)
RCM1 21 22 79.6E3
                                                     .ENDS AD8542
CCM1 21 22 100E-12
RCM2 22 98 50
* PSRR=90dB, ZERO AT 200Hz
RPS1 70 0 1E6
RPS2 71 0 1E6
CPS1 99 70 1E-5
CPS2 50 71 1E-5
EPSY 98 72 POLY(2) (70,0) (0,71) 0 1 1
RPS3 72 73 1.59E6
CPS3 72 73 500E-12
RPS4 73 98 25
```

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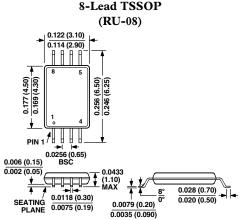
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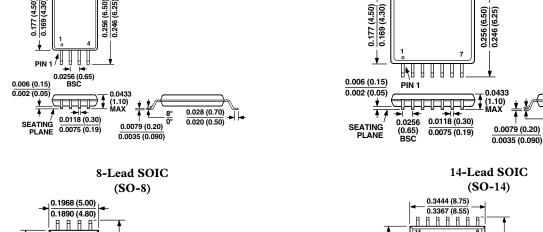
0.020 (0.50)

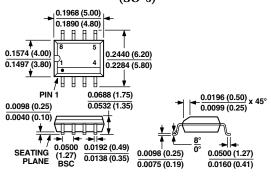
## AD8541/AD8542/AD8544

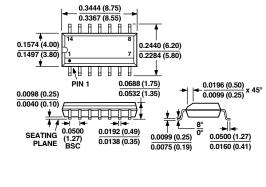
#### **OUTLINE DIMENSIONS**

Dimensions shown in inches and (mm).









14-Lead TSSOP

(RU-14)

0.201 (5.10) 0.193 (4.90)

14

